

Mechanisms & Applications of Quantum Tunneling in Quantum Dots, Nanowires and Tunnel Junctions

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www.jrasb.com || Vol. 4 No. 5 (2025): October Issue

Received: 17-10-2025

Revised: 21-10-2025

Accepted: 27-10-2025

ABSTRACT

Quantum tunneling is a fundamental quantum-mechanical phenomenon that enables particles to traverse potential barriers even when their classical energy is insufficient for surmounting them. At nanoscale dimensions, tunneling governs transport behaviour, influencing charge conduction, spin dynamics, quantum coherence, and device switching characteristics. This research describes in-depth an entire tunneling mechanisms assessment that covers different applications in quantum dots, nanowires, and tunnel junctions' industries. The papers major points were theoretical concepts, device-dependent tunneling effects, fabrication issues, and new uses in quantum computing, spintronics, nano-optoelectronics, neuromorphic computing, and energy systems. The comparison is made among three different types of nanostructures, and the areas of research that will be most likely affected by the progress of materials and quantum engineering techniques are pointed out.

Keywords- Quantum Tunneling, Quantum Dots, Nanowires, Tunnel Junctions.

I. INTRODUCTION

Quantum tunneling represents a remarkable feature of quantum mechanics that even goes against the classical way of thinking by letting electrons, holes, and other quasiparticles traverse barriers without having enough kinetic energy to get through them. As devices shrink to nanometer dimensions, tunneling moves from a marginal contribution to a dominant factor governing electron transport. The prowess of controlling tunneling probabilities by means of confinement, barrier thickness, interface quality, and extra forces has given rise to the ultrahigh-performing nanoscale devices and quantum parts.

Tunneling is of utmost significance in the three categories: quantum dots (QDs), nanowires (NWs), and tunnel junctions (TJs). Quantum dots act as synthetic atoms with no colors, and that is why tunneling is crucial for the transit of single electrons and the practice of qubit manipulation. Nanowires possess a one-dimensional structure and thus, gain the benefits of tunneling spectroscopy and ballistic conduction by virtue of their

boosted coherence and quantized conductance properties. Tunnel junctions—ranging from simple metal–insulator–metal structures to magnetic and superconducting junctions—allow precise manipulation of tunneling currents and coherent pair transport.

Understanding tunneling in these systems is very important for the creation of devices such as single-electron transistors, quantum logic gates, Josephson junction qubits, magnetic memory, high-frequency diodes, & ultrasensitive sensors throughout this process for the given research paper for further process.

II. THEORETICAL BACKGROUND OF QUANTUM TUNNELING

2.1 Schrödinger Equation and Barrier Penetration

Quantum tunneling is a phenomenon that manifests due to the overall wave-based nature of particles, as described by the Schrödinger equation. When a wavefunction meets a potential barrier, it shows an exponential decrease in amplitude inside the barrier, but

it still has a non-zero value, which gives rise to a small probability of getting through.

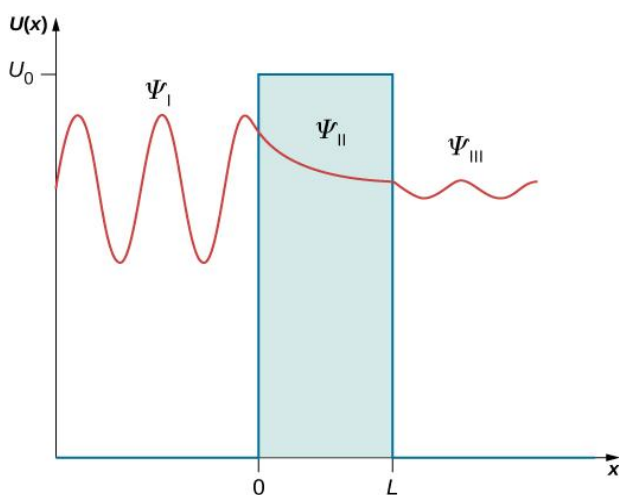
The probability of tunneling through a square barrier of height (V_0) and width (a) is given by:

The dependence on barrier width and height in a mathematical form of an exponential function brings out the importance of dimensions at the nanoscale.:

$$T \approx \frac{1 + (V_0^2 \cdot \sinh^2(\kappa a))}{4 \cdot E \cdot (V_0 - E)}$$

$$\kappa = \sqrt{\frac{2 \cdot m \cdot (V_0 - E)}{\hbar^2}}$$

The exponential dependence on this type of barrier width & height underscores the importance of nanoscale dimensions.

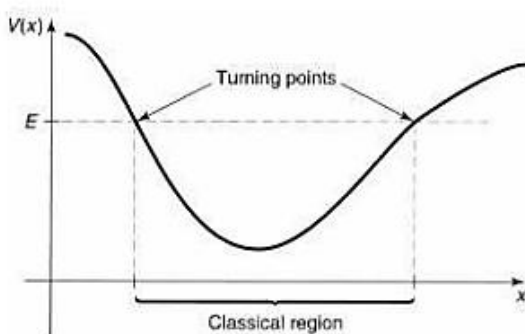


2.2 Wentzel-Kramers-Brillouin (WKB) Approximation

The WKB approximation offers some prospected semiclassical method for overall calculating tunneling probability across smoothly fluctuating potentials in this nature. It is fully and particularly advantageous for authentic barriers which are present in quantum dots and nanowires.

$$T \approx \exp\left(-2 \int_{x_1}^{x_2} \sqrt{\frac{2m[V(x) - E]}{\hbar^2}} dx\right)$$

This model explains many observed tunneling phenomena, including Fowler–Nordheim field emission and resonant tunneling.



2.3 Quantum Confinement Effects

Quantum confinement alters allowable energy states. In:

- Quantum dots (0D): energy levels become more discrete in this way.
- Nanowires (1D): energy sub bands create a form due to radial confinement here.
- Ultra-thin tunnel barriers: interface states & image-charge effects influence barrier shape here for further process.

Confinement enhances the overall sensitivity of tunneling to maintain external influences such as gate fields, strain, & magnetic fields.

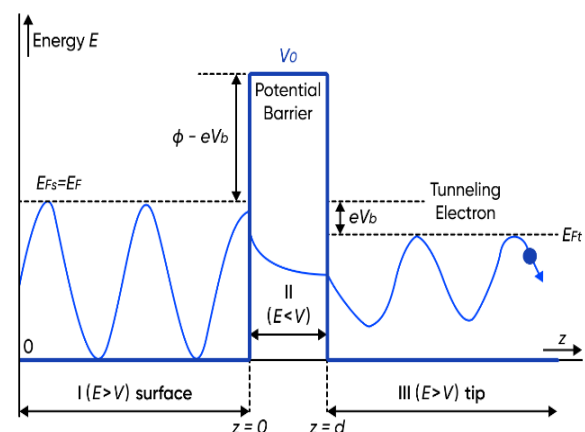
2.4 Density of States (DOS)

Tunneling rates depend on the variations of DOS in the electrodes and the confined region. For example:

- 0D DOS → delta-function-like peaks
- 1D DOS → Van Hove singularities
- 2D interfaces → constant DOS These variations normally strongly shape the tunneling conductances & current–voltage characteristics.

III. QUANTUM TUNNELING IN QUANTUM DOTS

Quantum dots function as synthetic based atoms & there are generally situated amid metallic, semiconducting, or the superconducting leads which are available. Tunneling in quantum dots is dictated by quantized energy levels, Coulomb charging power, & energy level alignment.



3.1 Key Tunneling Mechanisms

Sequential tunneling: electrons tunnel one at a time in here to be used which specify when energy levels align with lead Fermi levels here.

Resonant tunneling: this thing occurs when quantum dot energy levels coincide with the applied bias window.

Coulomb blockade: forbids tunneling unless the applied bias surpasses the charging energy.

Co-tunneling: higher-order tunneling where electrons tunnel through virtual states.

These mechanisms are observed in transport spectroscopy and stability diagrams (Coulomb diamonds).

3.2 Single-Electron Transistors (SETs)

Quantum dots form the central island of SETs. Gate electrodes tune energy levels, modulating tunneling rates. SETs offer extremely high charge sensitivity and operate as: electrometers, charge qubits, sensitive detectors for radiation and biomolecules.

3.3 Spin-Dependent Tunneling and Spin Qubits

Quantum dots confine single electrons whose spin states serve as qubits. Tunneling plays roles in:

- spin initialization,
- spin readout (spin-to-charge conversion),
- exchange coupling between neighboring dots.
- Spin-selective tunneling enables spin filters and quantum logic gates.

3.4 Optical Tunneling and Hot-Carrier Extraction

In quantum-dot optoelectronics, tunneling controls carrier escape rates and hence affects photoluminescence lifetimes, quantum efficiency, and hot-carrier extraction in solar cells.

IV. TUNNELING IN NANOWIRES

Nanowires provide quasi-one-dimensional channels with quantum confinement and ballistic transport characteristics. Their long aspect ratio and small diameters intensify tunneling interactions.

4.1 One-Dimensional Electron Transport

As electrons move through nanowires, phase coherence can be preserved over long distances, enabling phenomena such as quantized conductance and Fabry–Perot interference. Tunneling at contacts critically determines overall conductance.

4.2 Field-Induced Tunneling and Fowler–Nordheim Emission

Strong electric fields at nanowire tips enhance field emission, relevant for the following:

- vacuum nanoelectronics un this process,
- cold-cathode emitters for further aspects,
- sensing applications to complete it.

4.3 Quantum Interference and Tunneling Spectroscopy

Nanowires enable tunneling-based measurements of the following in here:

- conductance oscillations are needed
- Aharonov–Bohm effects are important in here
- Majorana bound states the nature in hybrid superconductor–nanowire devices are projected

4.4 Applications in Electronics, Sensing, and Quantum Information

- High-speed transistors show tunneling-driven injection reduces delay in this nature.
- Chemical & biological sensors clarify the adsorption modifies tunneling current.
- Topological quantum computing: tunneling spectroscopy is used to detect Majorana modes.

V. TUNNEL JUNCTIONS: MECHANISMS AND TECHNOLOGIES

Tunnel junctions here create a form which shows the backbone of spintronic memories, superconducting qubits, & high-speed diodes.

5.1 Metal–Insulator–Metal (MIM) Junctions

Electron tunneling across thin insulating barriers produces nonlinear current–voltage behavior. Applications include here for rectifiers, infrared detectors, & ultrafast electronic switches for further processing.

5.2 Magnetic Tunnel Junctions (MTJs)

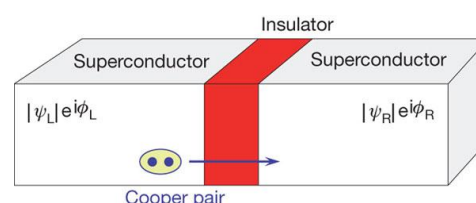
MTJs consist of two ferromagnetic layers separated by an insulator to project the scenerio. Their resistance depends thoroughly on magnetic alignment here:

- Parallel magnetization shows low resistance in this process.
- Antiparallel magnetization creates high resistance here.
- This tunneling magnetoresistance (TMR) effect more powers-based magnetic random-access memory (MRAM) with this.

5.3 Josephson Junctions

Josephson junctions allow overall Cooper pair tunneling, generating phenomena such as followings:

- DC Josephson effect is needed
- AC Josephson effect is considered important
- Macroscopic quantum coherence also needed for this.



They are essential in the following points:

- superconducting quantum processors are important
- SQUID magnetometers also important
- voltage standards mainly considered here as most eligible for the process

5.4 Other Tunnel Junctions

- Resonant tunneling diodes (RTDs) maintain and create the process withenable negative differential resistance.
- Thermionic and thermos-tunneling junctions here to improve more efficiency in energy conversion.

VI. COMPARATIVE ANALYSIS

6.1 Dimensionality and Tunneling Behavior

- QDs (0D): discrete levels → pronounced Coulomb blockade.

- NWs (1D): subbands $\rightarrow$ ballistic and interference effects.
- TJs (2D interfaces): tunneling dominated by barrier and interface properties.

6.2 Energy Scales and Dominant Mechanisms

- QDs: charging energy, level spacing.
- NWs: confinement energy, coherence length.
- JJs and MTJs: superconducting gap or spin polarization.

6.3 Fabrication and Engineering Considerations

Precise control of barrier thickness, surface quality, doping, & alignment which are critical for tunneling device reproducibility in this nature.

VII. EMERGING TRENDS AND FUTURE PROSPECTS

7.1 Quantum Information Technologies

Quantum computing relies purely & heavily on tunneling, particularly in: quantum-dot qubits, superconducting qubits alongside with topological qubits here can utilise the process here to understand the current situation.

7.2 Nano-optoelectronics

Tunneling-mediated mechanisms enhance performance in the following can be used photodetectors, LEDs & hot-carrier solar cells.

7.3 Energy Devices

Advanced tunneling concepts are being used in the following, thermotunneling power generators, tunneling-based thermoelectrics & other nanoscale photovoltaics.

7.4 Neuromorphic and Stochastic Computing

Tunneling devices exhibit a series of stochastic switching & nonlinear responses ideal for: artificial synapses along with probabilistic computing, in-memory processing-based architectures.

VIII. CONCLUSION

Quantum tunneling is an essential aspect of modern nanoscale engineering. The rules governing tunneling in the process of quantum dots, nanowires, & tunnel junctions drive through the developments in various fields like quantum computing, memory, sensing, energy conversion, or neuromorphic systems in this way to complete. As a result of achieving higher fabrication precision and the development of quantum materials, tunneling devices will be more and more influential in the future of nanoelectronics & quantum technologies.

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